

## OptiMOS® -T Power-Transistor



### Features

- N-channel - Enhancement mode
- AEC qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green package (RoHS compliant)
- Ultra low Rds(on)
- 100% Avalanche tested

| Type            | Package      | Marking |
|-----------------|--------------|---------|
| IPB180N03S4L-H0 | PG-TO263-7-3 | 4N03LH0 |

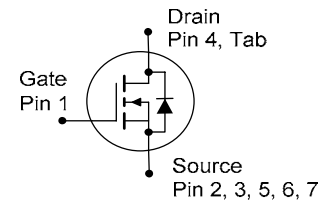
**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                                     | Symbol            | Conditions                                          | Value        | Unit |
|-----------------------------------------------|-------------------|-----------------------------------------------------|--------------|------|
| Continuous drain current                      | $I_D$             | $T_C=25\text{ °C}$ , $V_{GS}=10\text{ V}^{(1)}$     | 180          | A    |
|                                               |                   | $T_C=100\text{ °C}$ ,<br>$V_{GS}=10\text{ V}^{(2)}$ | 180          |      |
| Pulsed drain current <sup>(2)</sup>           | $I_{D,pulse}$     | $T_C=25\text{ °C}$                                  | 720          |      |
| Avalanche energy, single pulse <sup>(2)</sup> | $E_{AS}$          | $I_D=90\text{ A}$                                   | 980          | mJ   |
| Avalanche current, single pulse               | $I_{AS}$          | -                                                   | 180          | A    |
| Gate source voltage                           | $V_{GS}$          |                                                     | ±16          | V    |
| Power dissipation                             | $P_{tot}$         | $T_C=25\text{ °C}$                                  | 250          | W    |
| Operating and storage temperature             | $T_j$ , $T_{stg}$ |                                                     | -55 ... +175 | °C   |
| IEC climatic category; DIN IEC 68-1           |                   |                                                     | 55/175/56    |      |

### Product Summary

|              |      |    |
|--------------|------|----|
| $V_{DS}$     | 30   | V  |
| $R_{DS(on)}$ | 0.95 | mΩ |
| $I_D$        | 180  | A  |

PG-TO263-7-3



| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

### Thermal characteristics<sup>2)</sup>

|                                     |            |                                              |   |   |     |     |
|-------------------------------------|------------|----------------------------------------------|---|---|-----|-----|
| Thermal resistance, junction - case | $R_{thJC}$ | -                                            | - | - | 0.6 | K/W |
| SMD version, device on PCB          | $R_{thJA}$ | minimal footprint                            | - | - | 62  |     |
|                                     |            | 6 cm <sup>2</sup> cooling area <sup>3)</sup> | - | - | 40  |     |

### Electrical characteristics, at $T_j=25\text{ °C}$ , unless otherwise specified

#### Static characteristics

|                                  |               |                                                                         |    |      |      |               |
|----------------------------------|---------------|-------------------------------------------------------------------------|----|------|------|---------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$                                 | 30 | -    | -    | V             |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}$ , $I_D=200\text{ }\mu\text{A}$                          | 1  | 1.5  | 2.2  |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=30\text{ V}$ , $V_{GS}=0\text{ V}$ ,<br>$T_j=25\text{ °C}$      | -  | 0.01 | 1    | $\mu\text{A}$ |
|                                  |               | $V_{DS}=18\text{ V}$ , $V_{GS}=0\text{ V}$ ,<br>$T_j=85\text{ °C}^{2)}$ | -  | 5    | 60   |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=16\text{ V}$ , $V_{DS}=0\text{ V}$                              | -  | 1    | 100  | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=4.5\text{ V}$ , $I_D=90\text{ A}$                               | -  | 0.95 | 1.30 | m $\Omega$    |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=10\text{ V}$ , $I_D=100\text{ A}$                               | -  | 0.73 | 0.95 |               |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

### Dynamic characteristics<sup>2)</sup>

|                              |              |                                                                                  |   |       |       |    |
|------------------------------|--------------|----------------------------------------------------------------------------------|---|-------|-------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$<br>$f=1\text{ MHz}$                     | - | 17500 | 23000 | pF |
| Output capacitance           | $C_{oss}$    |                                                                                  | - | 3720  | 4800  |    |
| Reverse transfer capacitance | $C_{rss}$    |                                                                                  | - | 175   | 350   |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=15\text{ V}, V_{GS}=10\text{ V},$<br>$I_D=100\text{ A}, R_G=1.6\ \Omega$ | - | 9     | -     | ns |
| Rise time                    | $t_r$        |                                                                                  | - | 7     | -     |    |
| Turn-off delay time          | $t_{d(off)}$ |                                                                                  | - | 60    | -     |    |
| Fall time                    | $t_f$        |                                                                                  | - | 25    | -     |    |

### Gate Charge Characteristics<sup>2)</sup>

|                       |               |                                                                             |   |     |     |    |
|-----------------------|---------------|-----------------------------------------------------------------------------|---|-----|-----|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=24\text{ V}, I_D=180\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$ | - | 55  | 72  | nC |
| Gate to drain charge  | $Q_{gd}$      |                                                                             | - | 28  | 56  |    |
| Gate charge total     | $Q_g$         |                                                                             | - | 230 | 300 |    |
| Gate plateau voltage  | $V_{plateau}$ |                                                                             | - | 3.1 | -   | V  |

### Reverse Diode

|                                                |               |                                                                            |   |     |     |    |
|------------------------------------------------|---------------|----------------------------------------------------------------------------|---|-----|-----|----|
| Diode continuous forward current <sup>2)</sup> | $I_S$         | $T_C=25\text{ °C}$                                                         | - | -   | 180 | A  |
| Diode pulse current <sup>2)</sup>              | $I_{S,pulse}$ |                                                                            | - | -   | 720 |    |
| Diode forward voltage                          | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=100\text{ A},$<br>$T_j=25\text{ °C}$               | - | 0.9 | 1.3 | V  |
| Reverse recovery time <sup>2)</sup>            | $t_{rr}$      | $V_R=20\text{ V}, I_F=100\text{ A},$<br>$di_F/dt=100\text{ A}/\mu\text{s}$ | - | 250 | -   | ns |
| Reverse recovery charge <sup>2)</sup>          | $Q_{rr}$      |                                                                            | - | 280 | -   | nC |

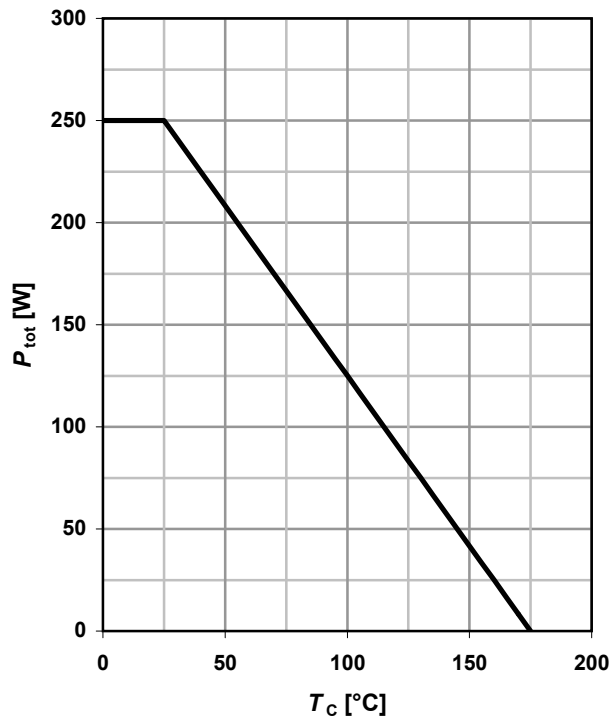
<sup>1)</sup> Current is limited by bondwire; with an  $R_{thJC} = 0.6\text{ K/W}$  the chip is able to carry 400A at 25°C.

<sup>2)</sup> Defined by design. Not subject to production test.

<sup>3)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

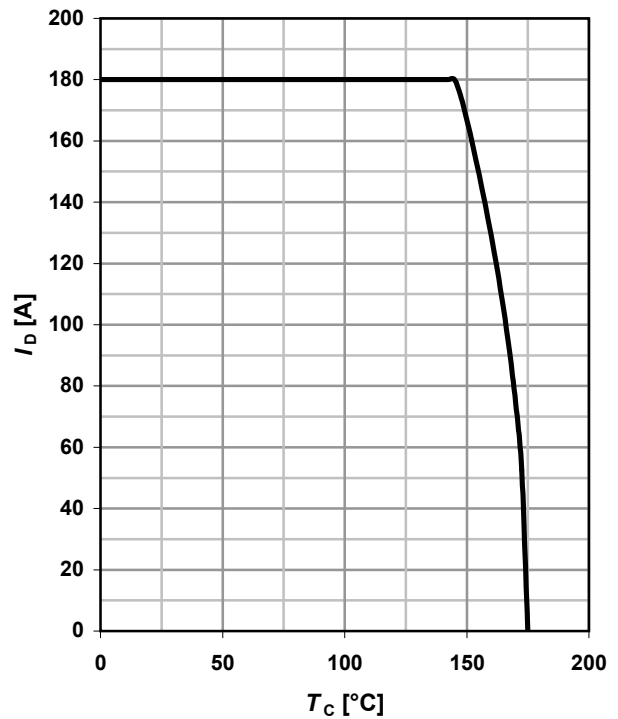
### 1 Power dissipation

$$P_{\text{tot}} = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



### 2 Drain current

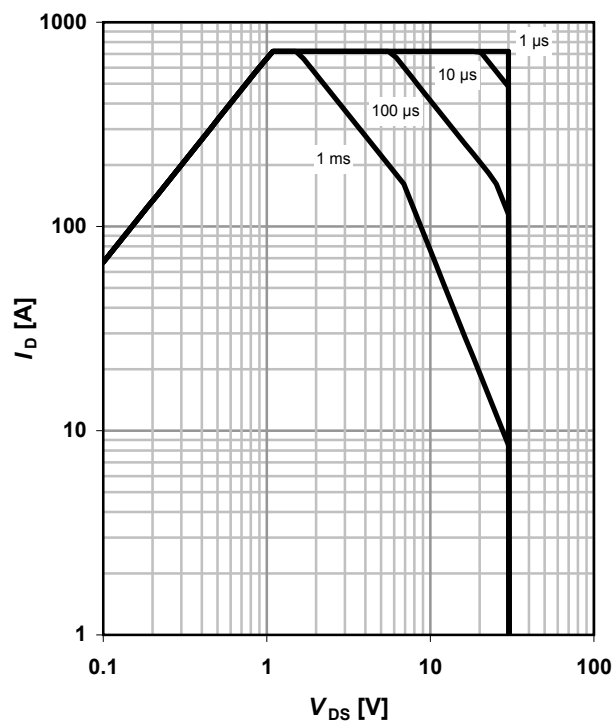
$$I_D = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



### 3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25^\circ\text{C}; D = 0$$

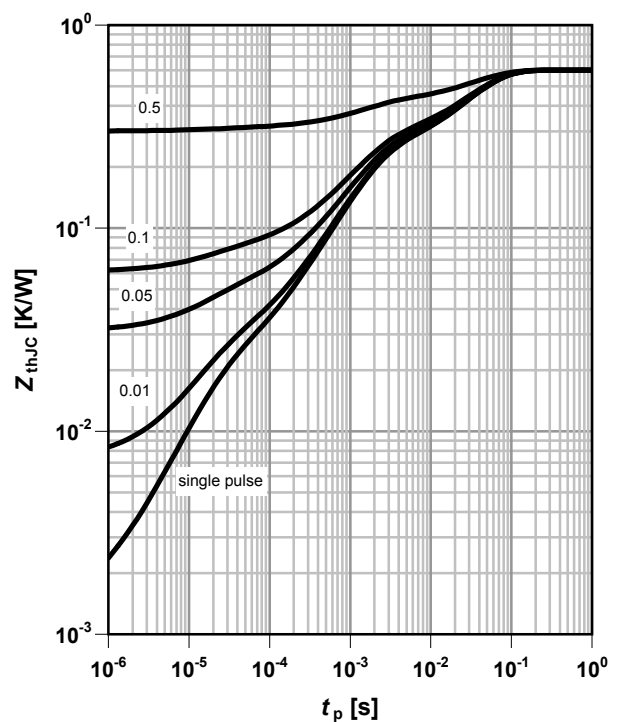
parameter:  $t_p$



### 4 Max. transient thermal impedance

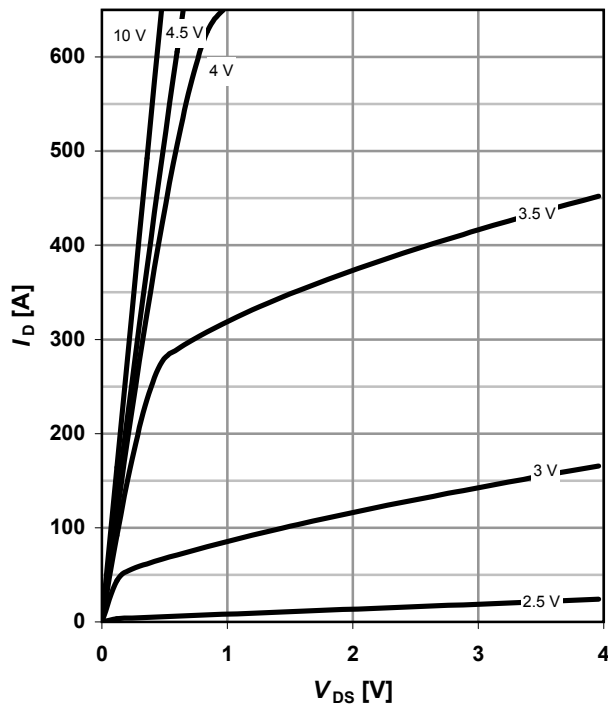
$$Z_{\text{thJC}} = f(t_p)$$

parameter:  $D = t_p/T$



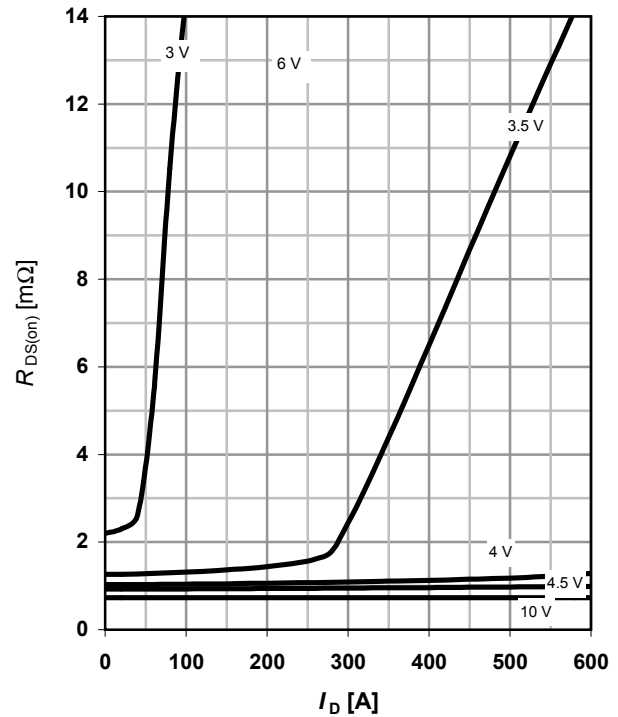
## 5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$ 

parameter:  $V_{GS}$ 


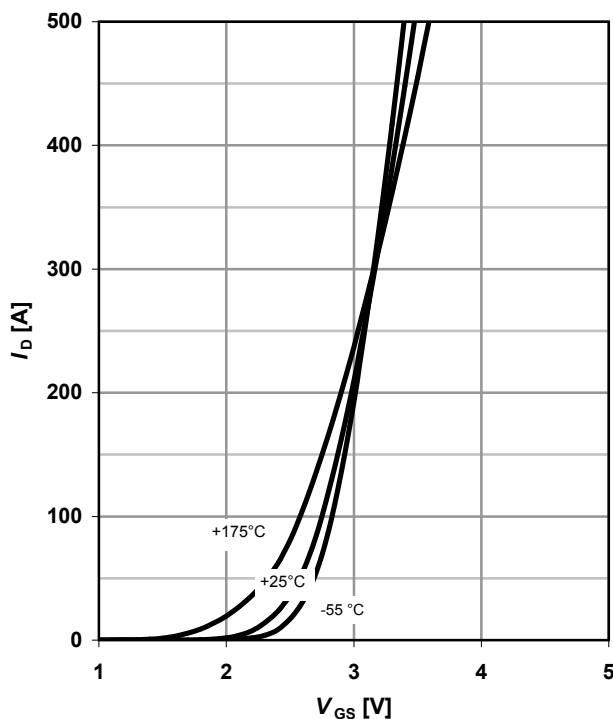
## 6 Typ. drain-source on-state resistance

 $R_{DS(on)} = (I_D); T_j = 25^\circ\text{C}$ 

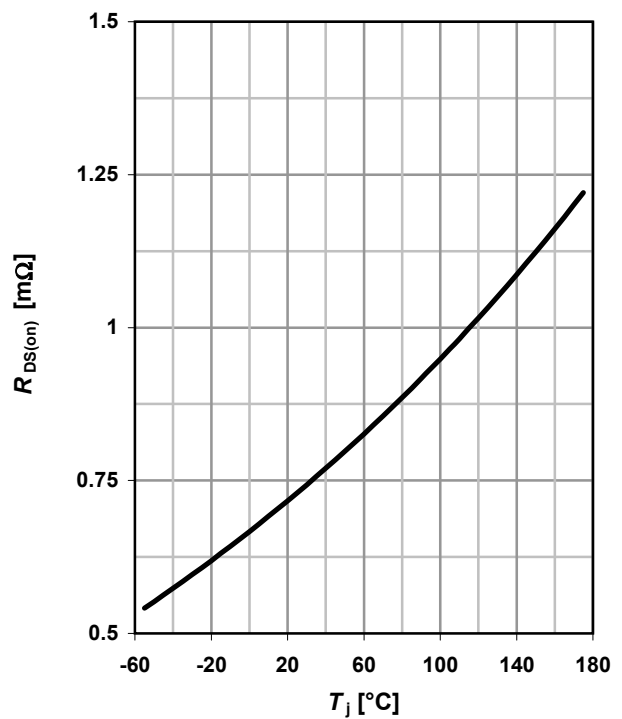
parameter:  $V_{GS}$ 


## 7 Typ. transfer characteristics

 $I_D = f(V_{GS}); V_{DS} = 6\text{ V}$ 

parameter:  $T_j$ 


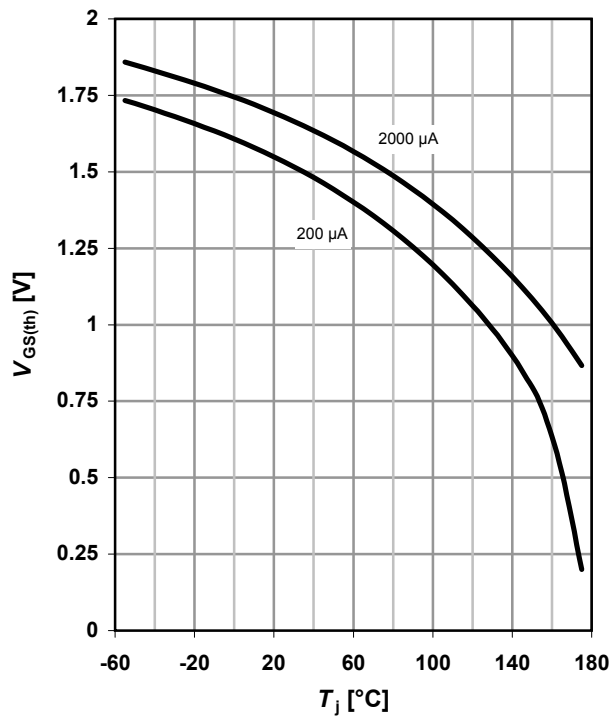
## 8 Typ. drain-source on-state resistance

 $R_{DS(on)} = f(T_j); I_D = 80\text{ A}; V_{GS} = 10\text{ V}$ 


## 9 Typ. gate threshold voltage

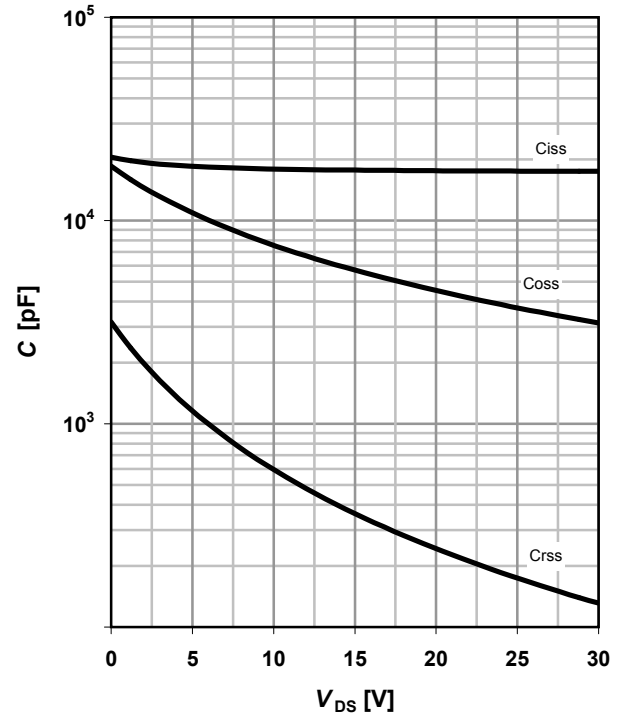
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter:  $I_D$



## 10 Typ. capacitances

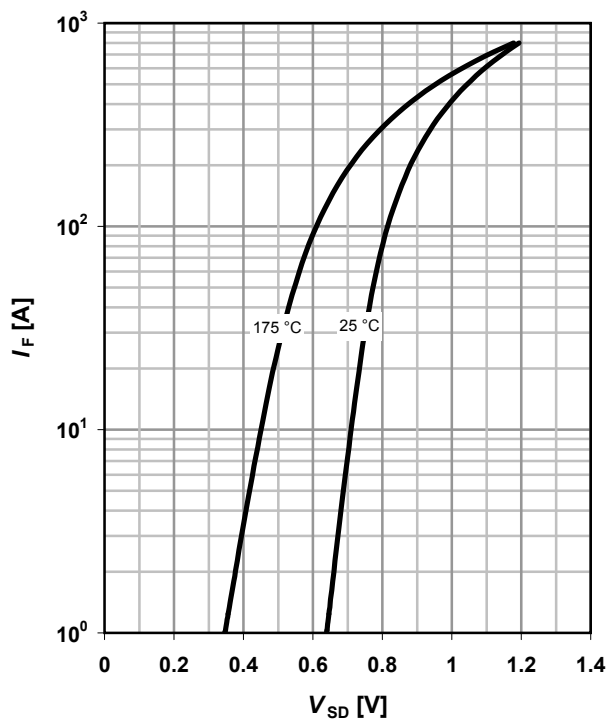
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



## 11 Typical forward diode characteristics

$$I_F = f(V_{SD})$$

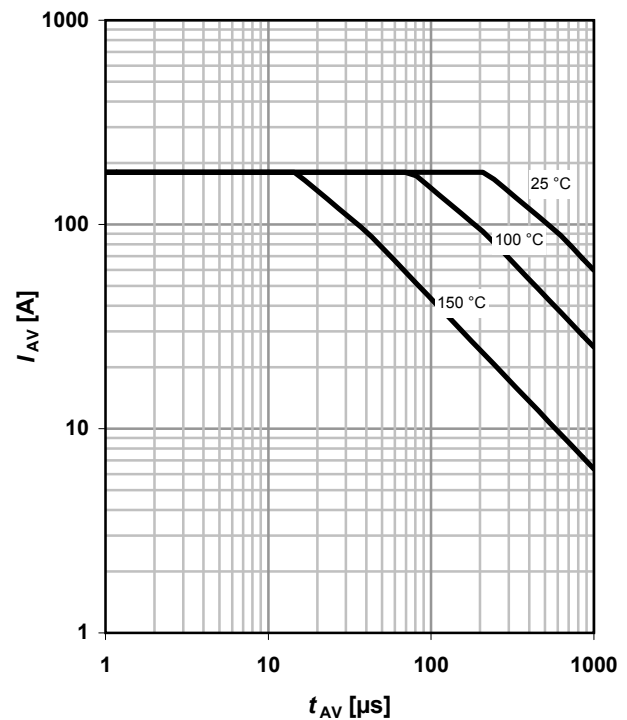
parameter:  $T_j$



## 12 Typ. avalanche characteristics

$$I_{AS} = f(t_{AV})$$

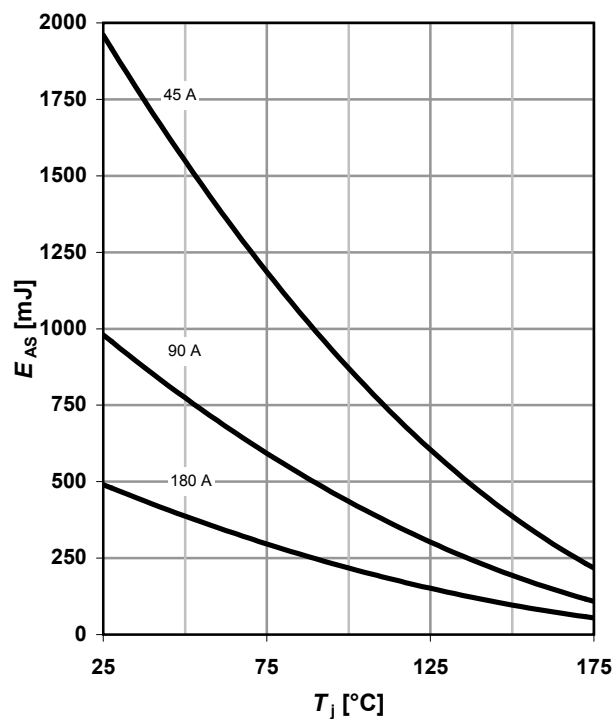
parameter:  $T_{j(start)}$



### 13 Typical avalanche energy

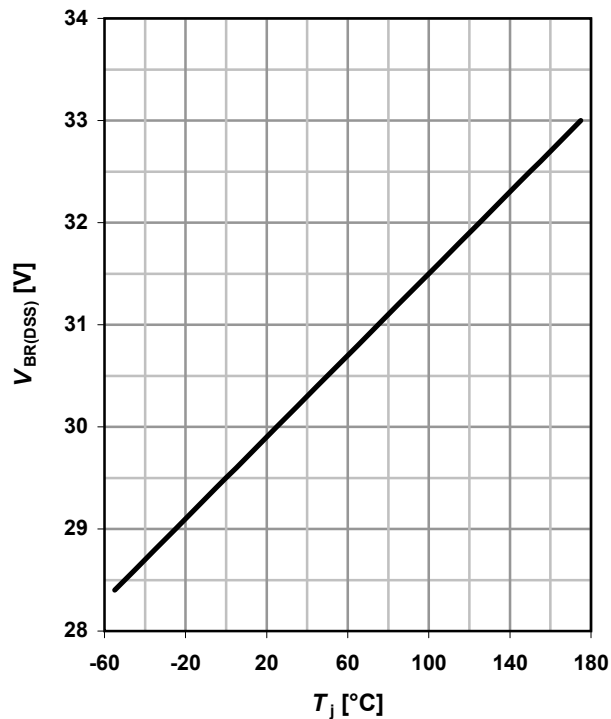
$$E_{AS} = f(T_j)$$

parameter:  $I_D$



### 14 Drain-source breakdown voltage

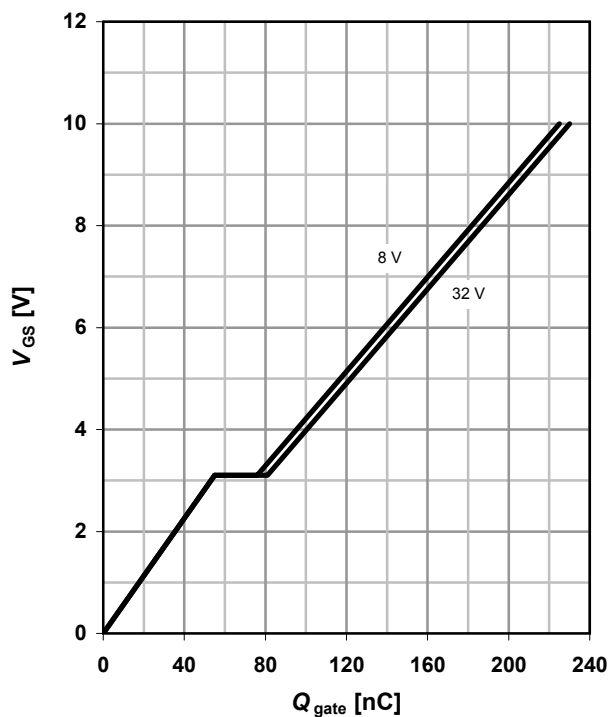
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$



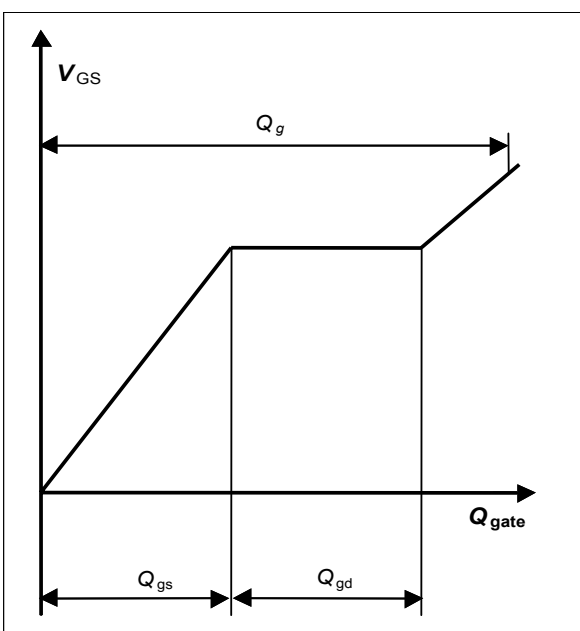
### 15 Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = 180 \text{ A pulsed}$$

parameter:  $V_{DD}$



### 16 Gate charge waveforms



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Revision History

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| Version | Date | Changes |
|---------|------|---------|
|         |      |         |

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